

Serial No. NEW

IIZ.003D2C

Preliminary Amendment dated October 22, 2003

Amendments to the Specification

Kindly amend the specification as follows:

Page 1, between the title and the heading "BACKGROUND OF THE INVENTION", insert

--CROSS REFERENCE TO RELATED APPLICATIONS

This is a continuation application of application Serial No. 09/920,713, filed August 3, 2001, which is a divisional application of application Serial No. 09/580,624, now U.S. Patent No. 6,281,111, filed May 30, 2000, which is a divisional application of application Serial No. 08/959,667, now U.S. Patent No. 6,097,091, filed October 29, 1997, which are hereby incorporated by reference in their entirety for all purposes.--

Please replace the title with the following amended title:

A METHOD FOR FABRICATING A SEMICONDUCTOR APPARATUS AND
METHOD FOR FABRICATING THE SAME INCLUDING A SEALING MEMBER WITH
REDUCED THERMAL STRESS

Please replace the abstract with the following amended abstract:

A semiconductor apparatus includes having a semiconductor substrate integrated circuit including an integrated circuit and an insulative base member a conductive pattern; an insulating layer which is formed on a main surface thereof. the semiconductor integrated circuit to forms a plurality of base members having uneven

heights; an opening which A conductive layer is formed on the main surface of the semiconductor substrate as coupled to the integrated circuit and includes an external portion that extends onto a through the insulating layer to expose a part of the conductive pattern; and a conductive layer which is formed on the insulating layer and the opening, the conductive layer is extending from the exposed portion of the conductive pattern to the top surface of the highest base member. A sealing member is formed on the main surface of the semiconductor substrate, the conductive layer and side surfaces of the base member, whereby the extended portion of the conductive layer is exposed from the sealing member An electrode is composed of the insulating layer, the opening and the conductive layer.